

## Supplementary material

# Sequential Solvent Casting for Improving the Structural Ordering and Electrical Characteristics of Polythiophene Thin Films

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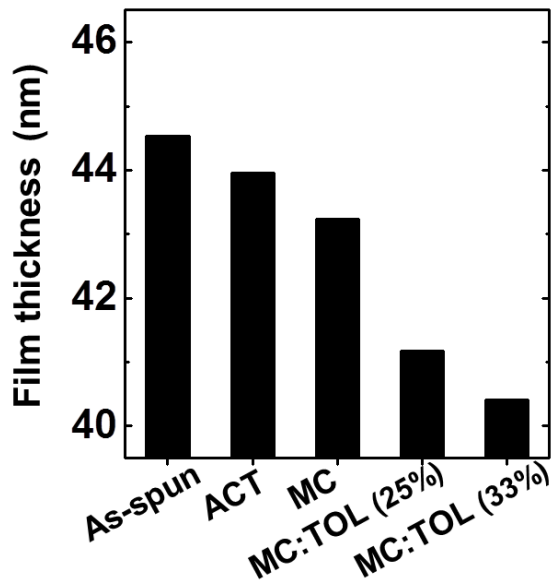
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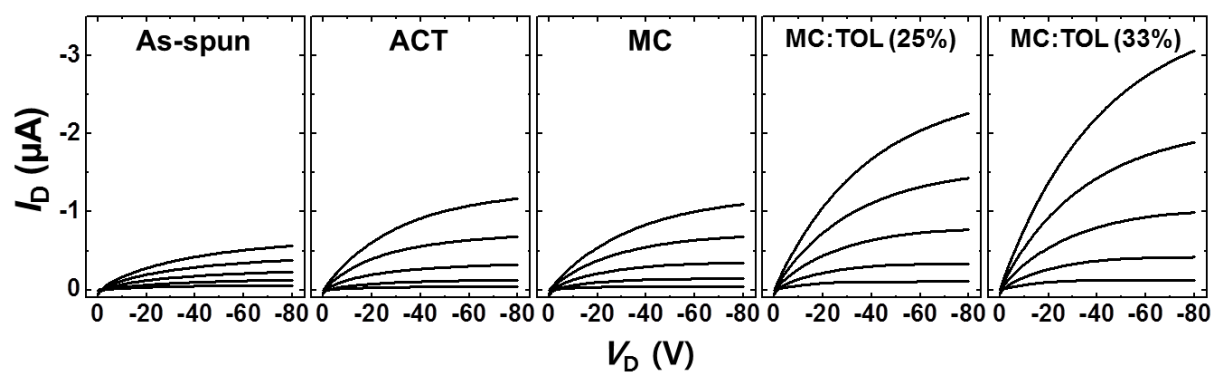
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**Figure S1.** Thickness values of the P3HT films: as-spun or exposed to the various solvents.



**Figure S2.** Output characteristics ( $I_D$ - $V_D$ ) of FETs ( $V_G$  steps: 0, -20, -40, -60, -80 V) fabricated using the P3HT thin films exposed to the various solvents.

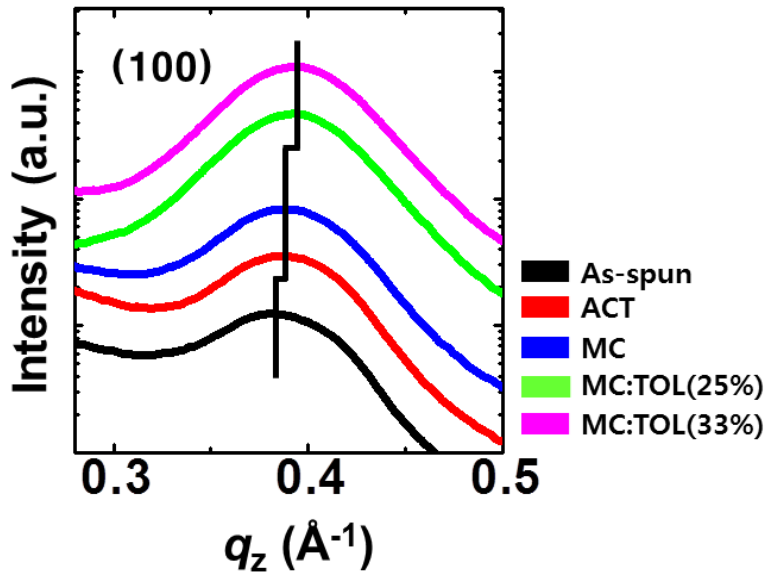


Figure S3. Magnified X-ray intensity profiles of the out-of-plan (100) reflections.